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Abbreviations

Abbreviation	Full name
AES	Auger Electron Spectroscopy
AFM	Atomic Force Microscopy
CCD	Charge-Coupled Device
CEM	Channeltron Electron Multiplier
CMA	Cylindrical Mirror Analyzer
DCRC-XRD	Double Crystal Rocking Curve X-Ray Diffraction
FWHM	Full Width at Half Maximum
IMPF	Inelastic Mean Free Path
IR	Infra-Red
LEED	Low Energy Electron Diffraction
MBE	Molecular Beam Epitaxy
MCP	Multi Channel Plate
MCT	Mercury Cadmium Telluride
ML	MonoLayer
PEEM	Photo Electron Emission Microscope
RHEED	Reflection High Energy Electron Diffraction
SEM	Scanning Electron Microscopy
STM	Scanning Tunneling Microscopy
TEM	Transmission Electron Microscopy
UHV	Ultra High Vacuum
UV	Ultra Violet
XPS	X-ray Photoelectron Spectroscopy
XRD	X-Ray Diffraction